

Supporting information

Photocarrier relaxation pathway in selenium quantum dots and its application for UV-Vis photodetecting

Xiantao Jiang^{†,1,3}, Weichun Huang^{†,1,2}, Rui Wang¹, Hongbo Li¹, Xuefeng Xia¹, Xuemei Zhao¹, Lanping Hu², Tingting Chen², Yanfeng Tang², Han Zhang^{*,1}

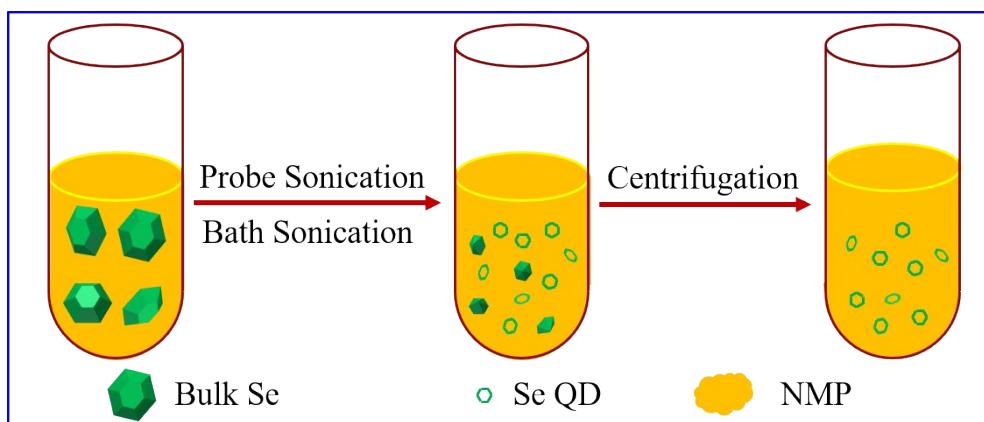
¹Shenzhen Engineering Laboratory of Phosphorene and Optoelectronics, Collaborative Innovation Center for Optoelectronic Science and Technology, College of Optoelectronic Engineering, Shenzhen University, Shenzhen 518060, China

²College of Chemistry and Chemical Engineering, Nantong University, Nantong 226019, Jiangsu, P. R. China

³College of Chemistry and Environmental Engineering, Shenzhen University, Shenzhen, 518060, China

[†]These authors contribute equally to this manuscript.

*Corresponding author: hzhang@szu.edu.cn



Scheme S1. The schematic diagram of Se QDs fabrication.

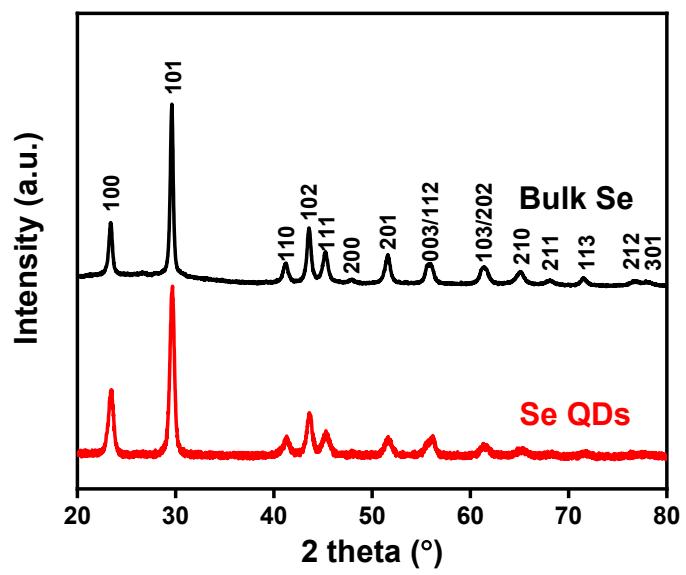


Figure S1. XRD patterns of bulk Se and Se QDs.

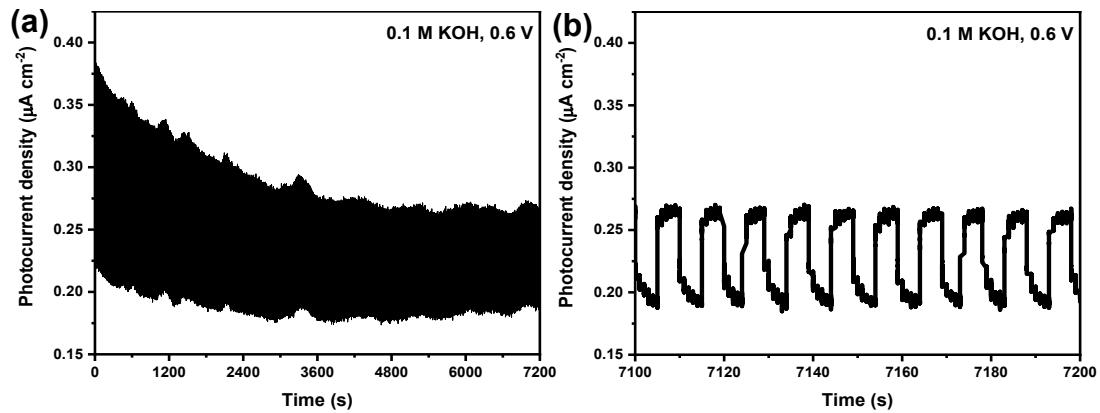


Figure S2. (a) The stability measurement of the as-prepared Se QDs after being stored in 0.1 M KOH for 1 month in 0.1 M KOH at a bias voltage of 0.6 V. (b) the selected area in (a).